

P/N: YZPST-3M2T020Y36

DOUBLE THYRISTOR MODULE; 3600 V

Maximum Ratings

Symbol	Condition	Ratings	Unit
$I_{T(AV)}$	Single phase, half wave, 85° conduction $T_c=85^\circ\text{C}$	115	A
I_{TRMS}	Single phase, half wave, 85° conduction	180	A
I_{TSM}	$T_c=125^\circ\text{C}$	2500	A
I^2t	$T_c=125^\circ\text{C}$	30	kA^2S
V_{DRM}/V_{RRM}	$T_c=125^\circ\text{C}$	3600/3600	V
di/dt	non-repetitive	200	A/us
V_{iso}	A.C.1m/1S	3000/3600	V
T_j		-40 ~ +125	$^\circ\text{C}$
T_{stg}		-40 ~ +125	$^\circ\text{C}$
W		350	g

Electrical Characteristics

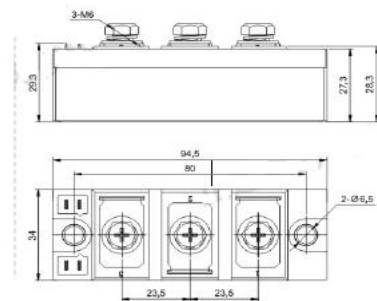
Symbol	Condition	Ratings	Unit
I_{DRM}/I_{RRM}	At V_{DRM} , Single phase, half wave, $T_c=125^\circ\text{C}$	70	mA
V_{TM}	On-State Current 500A, $T_j=25^\circ\text{C}$	2.45	V
$V_{T(TO)}$	$T_j=125^\circ\text{C}$	0.95	V
r_t	$T_j=125^\circ\text{C}$	3.0	$\text{m}\Omega$
t_{gd}	$T_j=25^\circ\text{C}$	3	us
t_q	$T_j=125^\circ\text{C}$	400	us
I_{GT}/V_{GT}	$T_j=25^\circ\text{C}$	250 / 2.5	mA/V
V_{GD}	$V_D=67\%V_{DRM}$, $T_j=125^\circ\text{C}$	0.25	V
DV/DT	$V_D=67\%V_{DRM}$	1000	V/us
I_H	$T_j=25^\circ\text{C}$	250	mA
I_L	$T_j=25^\circ\text{C}$	500	mA
$R_{th(j-c)}$	Per Module	0.095	$^\circ\text{C}/\text{W}$
$R_{th(c-h)}$	Per Module	0.03	$^\circ\text{C}/\text{W}$

14. QUALITY REQUIREMENTS:

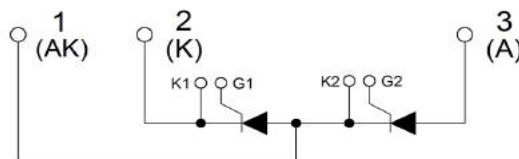
Elements must be packaged in such a fashion as to prevent any damage, contamination or degradation in shipping. Vendor must maintain lot identification and traceability records to assure sufficient control of material, process and product integrity in the event of a product recall.

15 ADDITIONAL REQUIREMENTS

Outline Drawing



MT3-115-36-F



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